

Si PNP TRANSISTOR

2SA573, 2SA574

EPOXY MOLDED, AUDIO AMP., RF AMP., SWITCHING

■ ABSOLUTE MAXIMUM RATINGS ($T_a : 25^\circ\text{C}$)

		2SA573	2SA574	
COLLECTOR-BASE VOLTAGE	V_{CBO}	-30	-60	V
COLLECTOR-EMITTER VOLTAGE	V_{CEO}	-25	-50	V
EMITTER-BASE VOLTAGE	V_{EBO}	-5	-5	V
COLLECTOR CURRENT	I_C	-100	-100	mA
POWER DISSIPATION	P_C	300	300	mW
JUNCTION TEMPERATURE	T_J	125	125	$^\circ\text{C}$
STORAGE TEMPERATURE	T_{stg}	-55~+125	-55~+125	$^\circ\text{C}$

■ ELECTRICAL CHARACTERISTICS ($T_a : 25^\circ\text{C}$)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
COLLECTOR CUTOFF CURRENT	I_{CBO}	$V_{CB} : -20\text{V}, I_E : 0$			-100	nA
STATIC FWD. CUR. TRANSFER RATIO	h_{FE}	$V_{CE} : -6\text{V}, I_C : -1\text{mA}, \text{NOTE 1}$	30		800	
TRANSITION FREQUENCY	f_T	$V_{CE} : -10\text{V}, I_E : 2\text{mA}$	80	150		MHz
COLLECTOR OUTPUT CAPACITANCE	C_{ob}	$V_{CB} : -10\text{V}, I_E : 0, f : 1\text{MHz}$		4	10	pF
BASE-COLLECTOR TIME CONSTANT	$C_{eTb'b}$	$V_{CB} : -10\text{V}, I_E : 2\text{mA}, f : 31.9\text{MHz}$		50	150	ps
COLLECTOR-EMITTER SATURATION VOLTAGE	$V_{CE(sat)}$	$I_C : -50\text{mA}, I_B : -10\text{mA}$			-0.3	V
BASE-EMITTER SATURATION VOLTAGE	$V_{BE(sat)}$	$I_C : -50\text{mA}, I_B : -10\text{mA}$			-1.0	V

NOTE 1 : ACCORDING TO THE VALUE OF h_{FE} , THE DEVICES ARE CLASSIFIED AS FOLLOWS.

RANK 1 : 30~70

RANK 2 : 60~120

RANK 3 : 90~180

RANK 4 : 150~350

RANK 5 : 250~500

RANK 6 : 400~800

NOTE 2 : FOR COMPLEMENTARY CIRCUITS USING 2SA573 AND 2SA574, NPN DEVICES TYPE 2SC950 AND 2SC951 ARE RESPECTIVELY AVAILABLE FOR REQUEST.

